Abstracts

A 22--24-GHz Cryogenically Cooled GaAs FET Amplifier

A. Cappello and J. Pierro. "A 22--24-GHz Cryogenically Cooled GaAs FET Amplifier." 1984 Transactions on Microwave Theory and Techniques 32.3 (Mar. 1984 [T-MTT] (Special Issue on Power and Low-Noise GaAs FET Circuits and Applications)): 226-230.

This paper describes the design and performance of a cryogenically cooled low-noise FET amplifier operating in the 22-24-GHz range. The amplifier employs five cascaded single-ended gain stages and an integral bandpass filter. Noise temperatures in the 200 K range with an associated gain of 28 dB are typical for the nine cooled units built to date.

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